

DIE NO. **2C5583** — PNP
 LINE SOURCE — RF502.59

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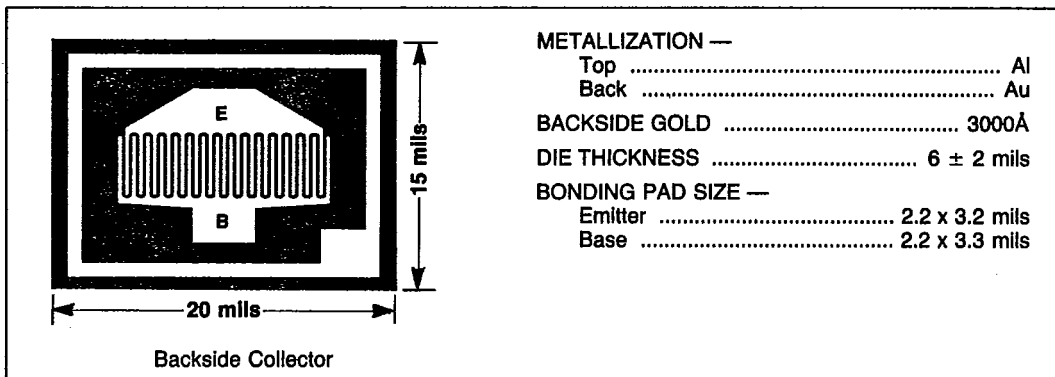


This die provides performance equal to or better than that of the following device types:

2N5583

High-frequency low-to-medium power PNP transistor designed for class A, B and C amplifiers, oscillators, mixers, multipliers and high-speed switches in the 1-1000 MHz frequency range.

- $f_T \leq 1.3$ GHz @ 10V/100 mA



METALLIZATION —

Top Al
 Back Au

BACKSIDE GOLD 3000Å

DIE THICKNESS 6 ± 2 mils

BONDING PAD SIZE —

Emitter 2.2×3.2 mils
 Base 2.2×3.3 mils

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, Note 1)

Parameter	Test Conditions	Min	Max	Unit
BV_{CEO}	$I_C = 10$ mAdc	30	—	Vdc
BV_{CBO}	$I_C = 10$ μ Adc	30	—	Vdc
BV_{EBO}	$I_E = 100$ μ Adc	3.0	—	Vdc
I_{CBO}	$V_{CB} = 20$ Vdc	—	50	nAdc
h_{FE1}	$V_{CE} = 2.0$ Vdc, $I_C = 40$ mAdc	20	—	—
h_{FE2}	$V_{CE} = 2.0$ Vdc, $I_C = 100$ mAdc	25	100	—
h_{FE3}	$V_{CE} = 5.0$ Vdc, $I_C = 300$ mAdc	15	—	—
$V_{CE(sat)}$	$I_C = 100$ mAdc, $I_B = 10$ mAdc	—	0.8	Vdc

- NOTES: 1. Because of the limitations of probe testing, only dc parameters are tested. These parameters must be measured using pulse techniques: pulse width ≤ 300 ns, duty cycle $\leq 2\%$.
2. Detailed device characteristics are available from your Motorola sales representative.